



PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

**KENNETH E. GONSALVES**

Serial No. **09/992,560**

Filed: **November 5, 2001**

For: **HIGH RESOLUTION RESISTS  
FOR NEXT GENERATION  
LITHOGRAPHIES**

Art Unit: **1752**

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**TC 1700**

**INFORMATION DISCLOSURE STATEMENT**

Assistant Commissioner for Patents  
Washington, DC 20231  
Sir:

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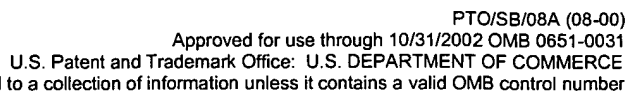
Respectfully submitted,

David E. Wigley, Ph.D.  
Reg. No. P52,362

**KILPATRICK STOCKTON LLP**  
1100 Peachtree Street  
Suite 2800  
Atlanta, Georgia 30309-4530  
(404) 815-6500  
Our Docket: 46872-257422

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231, on August 15, 2002.

David E. Wigley, Ph.D. - Reg. No. P52,362



## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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**Complete if Known**

<b>Application Number</b>	<b>9/992,560</b>
<b>Filing Date</b>	<b>November 5, 2001</b>
<b>First Named Inventor</b>	<b>KENNETH E. GONSALVES</b>
<b>Group Art Unit</b>	<b>1752</b>
<b>Examiner Name</b>	
<b>Attorney Docket Number</b>	<b>46872-257422</b>

Sheet	1	of	2
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## U.S. PATENT DOCUMENTS

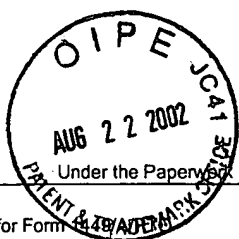
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## FOREIGN PATENT DOCUMENTS

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<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent document, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language translation is attached.



<b>Substitute for Form 159</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<b>Complete if Known</b>			
		<b>Application Number</b>	09/992,560		
		<b>Filing Date</b>	November 15, 2001		
		<b>First Named Inventor</b>	KENNETH E. GONSALVES		
		<b>Group Art Unit</b>	1752		
		<b>Examiner Name</b>			
<b>Sheet</b>	2	<b>of</b>	2	<b>Attorney Docket Number</b>	46872-257422

**OTHER INFORMATION - NON PATENT LITERATURE DOCUMENTS**

Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published

Examiner Initials	Cite No. <sup>1</sup>		T <sup>2</sup>
		KENNETH E. GONSALVES, et al., "Combinatorial approach for the synthesis of terpolymers and their novel application as very-high-contrast resists for x-ray nanolithography," J. Vac. Sci. Technol. B 18(1), Jan/Feb 2000, pp. 325-327.	
		YOUNQI HU, et al., "Nanocomposite resists for electron beam nanolithography," Microelectronic Engineering 56 (2001), pp. 289-294.	
		HENPENG WU, et al., "Incorporation of polyhedral oligosilsesquioxane in chemically amplified resists to improve their reactive ion etching resistance," J. Vac. Sci. Technol. B 19(3), May/Jun 2001, pp. 851-855.	
		HENGPENG WU, et al., "Synthesis and Characterization of Radiation-sensitive Polymers and Their Application in Lithography," Ph.D. dissertation, University of Connecticut, April 2001.	
		L. MERHARI, et al., "Nanocomposite resist systems for next generation lithography," Microelectronic Engineering (2002), article in press.	
		JOHN CANNING, "Next generation Lithography: When, why, and at what cost?" Microelectronic Engineering (2002), article in press, abstract only.	
		ROBERT L. BRAINARD, "Resists for next generation lithography," Microelectronic Engineering (2002), article in press.	
		SATOSHI SAITO, "A new positive electron-beam resist material composed of catechol derivatives," Microelectronic Engineering (2002), article in press.	
		HENGPENG WU, et al., "Preparation of a Photoacid Generating Monomer and Its Application in Lithography," Advanced Functional Materials, 11(4), August 2001, pp. 271-276.	
		HENGPENG WU, et al., "A Novel Single-Component Negative Resist for DUV and Electron Beam Lithography," Advanced Functional Materials, 13(3), February 2001, pp. 195-197.	

<b>Examiner Signature</b>		<b>Date Considered</b>	
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